

[54] ELECTROPHOTOGRAPHIC ELEMENT WITH ALPHA -SI AND C MATERIAL DOPED WITH H AND F AND PROCESS FOR PRODUCING THE SAME

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[57] ABSTRACT

An electrophotographic light-sensitive element and process for the production thereof are described, wherein the element comprises an electrically conductive support coated with a photoconductive layer composed of a silicon- and carbon-based amorphous material doped with hydrogen and fluorine.

18 Claims, 7 Drawing Figures

